

Large polaron evolution in anatase TiO₂ due to carrier and temperature dependence of electron-phonon coupling

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Abstract:

Electronic and magneto transport data of anatase TiO₂ are analyzed and modelled considering various polaronic effects. The unexpected positive dependence of mobility on carrier concentration is attributed to the screening of electron-phonon interaction by excess charge carriers. The linear and quadratic components in magnetoresistance are separately associated with the transport and trapping modes of the carrier. From those results, we can depict the evolution of large polaron versus temperature and carrier concentration, and clarify the physics behind ambiguous conduction behavior of anatase TiO₂.

Introduction:

The anatase structural phase of titanium dioxide (TiO₂) is one of the most widely applied semiconductors. Besides its famous photosynthetic ability, novel applications rely on the less well-known electronic properties were proposed recently, such as memristors¹, spintronic devices², transistor³ and transparent conducting oxides⁴. Stoichiometric anatase is an insulator with the band gap around 3.2 eV. The conductive samples, with intrinsic or extrinsic dopants, typically present with a carrier concentrations above 10¹⁷ cm⁻³ and a resistivity among 1 to 10⁻⁴ Ω·cm⁵⁻⁶.

The conductive behavior of anatase depends on temperature and carrier concentration under multiple mechanisms. From the view of lattice structure, anatase TiO₂ is a disorder system⁷. Below ~60K, variable range hopping (VRH)⁸ dominates and the dopants act as both trapping sites and disorder impurities, giving rise to the semiconductor behavior. When the electrons are thermally excited to conduction band, the dopants will only serve as scattering centers, resulting a metallic behavior. On the other hand, from the charge carrier perspective, electron in anatase TiO₂ would couple to phonon, trap itself and form the quasiparticle "large polaron"⁹⁻¹¹, an intermediate state between localized small polaron and free electron. Since the electron-phonon (e-ph) interaction is just moderate strong, the large polaron is easily

perturbed and tuned to different states like dissociation¹²⁻¹³, melting¹⁴⁻¹⁵ and crystallization¹⁶. However, although extensive theoretical work has been performed, due to the lack of experimental methods, tentative characterization on the coupling range have only been launched recently with instruments like ARPES¹⁰, RIXS¹¹ and STM⁷. Thus, few consistent description has yet been made on the polaron evolution, being a bottleneck for further research.

In this letter, we report on the polaron evolution in anatase TiO₂ over temperature and carrier concentration. Electronic and magnetic transport data from anatase TiO₂ thin films are used for exploring the polaron states. At the low and high temperature ranges, the resistivity shows semiconductor and metallic behavior, respectively, in agreement with previous studies. Unexpectedly, the mobility was found to increase with increasing carrier concentration. In the semiconductor phase, the higher hopping mobility results from an increase in hopping sites concentration. While, in the metallic phase, the increased mobility is attributed to a decrease in polaron effective mass due to a recently reported screening effect on e-ph coupling. We also find the magnetoresistance (MR) could be decomposed to a linear term and a quadratic term, separately characterizing the transport and trap behavior of carriers. Since different polaron states have different dependence on the temperature and carrier concentration, a phase diagram could be depicted through analyzation on the electronic and magneto transport data.

Fabrication Methods:

92nm (~100 monolayers) anatase TiO₂ thin films were grown on single crystal (100)-oriented LaAlO₃ substrates by pulsed laser deposition. All the samples were fabricated at 800°C under 3×10^{-3} mTorr oxygen partial pressure. The laser energy and frequency was kept at 1.33J/cm² and 2 Hz. To reflect the nature properties of anatase TiO₂, we choose to introduce the electrons with the intrinsic dopant of oxygen vacancy by the vacuum thermal annealing. To avoid possible influence of annealing, we annealed all the samples at same temperature (900°C) for same time (3 hours). Doping level is only tuned with variation in oxygen partial pressure (9×10^{-8} to 3×10^{-3} mTorr). The diffusion length of oxygen ions $l = \sqrt{Dt}$ is 600nm, where D is the oxygen diffusion coefficient¹⁷ and t is the annealing time. Since the diffusion length is much larger than the film thickness (~90nm), we can expect a homogenously distributed carrier concentration in the films.

Results

Crystal Quality

The X-ray diffraction (CuK α_1 ray) pattern of the TiO₂ films is shown in Figure 1 (a). The sharp TiO₂ (004) peaks indicate the well-kept anatase structure. A tiny diffuse of the Bragg peak is shown in Fig1(b), indicating the lattice is slightly distorted after reduction. The distortion could be attributed to two possible mechanisms: (1) the oxygen vacancies can be viewed as flaws in the lattice frame, broadening the Bragg peak; (2) the e-ph interaction could distort the lattice, cause a diffusive Bragg peak¹⁸. The first mechanism is acceptable since all the FWHM (γ) of reduced samples are larger than the oxygen rich sample (γ_0), $\gamma/\gamma_0 > 1$. Nevertheless, it cannot explain the lattice relaxation at $\sim 3 \times 10^{19}$ cm⁻³. which was reported as the criteria for a screening in e-ph coupling by excess carriers¹⁰. Thus, the relaxation could be

ascribed to the second mechanism: when the electron-lattice coupling is screened, the lattice will be relaxed from the distortion.

Electronic transport measurement

The transport properties of the anatase TiO₂ were measured by a Quantum Design Physical Properties Measurement System. The the resistivity of the samples range from 10⁻⁴ to 10⁻¹ Ω×cm [Fig.2(a)], covering most reported data⁶. The Hall mobility and carrier concentration is presented in Fig.2(b). Unexpectedly, with higher carrier concentration, the mobility is higher. In the low temperature range (<60K), the carrier transport is believed in variable range hopping mode⁸, corresponding to the semiconductor behavior, with¹⁹:

$$\rho = \rho_0 e^{\left(\frac{T_0}{T}\right)^{\frac{1}{4}}} \quad (1)$$

where ρ is the resistivity, T is the temperature, ρ_0 and T_0 are two parameter fitted by experimental data. In the hopping model, the higher mobility is easily understood with a increase in trapping sites density. While in the metallic phase, the large polarons are excited to the conduction band, moving coherently and scattered by LO phonons, with the mobility μ_{LO} ²⁰:

$$\mu_{LO} = \frac{\hbar}{2\alpha\hbar\omega_{LO}} \cdot \frac{e}{m_{LP}} \cdot \left(\frac{m_e^*}{m_{LP}}\right)^2 \cdot f(\alpha) \left(e^{\frac{\hbar\omega_{LO}}{k_B T}} - 1\right) \quad (2)$$

where e is electron charge, $\hbar$ is the reduced Plank's constant, ω_{LO} is the frequency of LO phonon involved in scattering, α is the electron phonon coupling constant, m_e^* is the band effective mass of the carrier, $m_{LP} = m_e^*(1 + \alpha/6)$ is the effective mass of the large polaron, $f(\alpha)$ is a slowly varying function ranging from 1.0 to 1.4, and longitudinal optical frequency of anatase TiO₂ is 366cm⁻¹²¹. The resistivity is fitted with the VRH model and the polaron model [Fig2(c)]. The calculated effective mass decrease with increasing carrier concentration, dropping from 0.63 m_e at 7×10¹⁸cm⁻³ to 0.47 m_e at 2×10²⁰cm⁻³, consistent with previous experimental result¹⁰ for low n_e (~0.7 m_e at 5×10¹⁸cm⁻³) and theoretical calculation in high n_e ($m_e^* = 0.43m_e$ for bare effective mass)²². Thus, the positive dependence of mobility on carrier concentration could be explained with the screening effect of the large polaron. Namely, as the carrier concentration increases, the e-ph interaction is gradually screened¹⁰. Since the effective mass of a large polaron is proportional to its self-trapping potential²³, and carrier mobility is inverse proportional to the effective mass, the mobility will increase as the e-ph coupling is weaken.

Magneto transport measurement

The temperature dependent MR are shown in Fig3(a). With the decrease of temperature, the MR gradually change from positive to negative. In the low temperature range (<60K), MR can be fitted with a superposition of a negative linear term and a quadratic term. The negative component has been widely studied, resulting from the quantum interference effect¹⁹. This negative MR happens when the carrier transport incoherently in an disorder system²⁴:

$$\ln\left(\frac{\rho(T,H)}{\rho(T,0)}\right) = -Av \frac{1-\alpha}{\alpha} \left(\frac{e}{\hbar c} \cdot H \cdot n^{-\frac{2}{3}}\right)^{\frac{1}{2v}} \cdot \ln\left(\frac{\rho(T)}{\rho_0}\right), (\nu \sim 0.5) \quad (3)$$

where A is a dimensionless coefficient decided by experimental results, ν is a factor around 0.5 and n is the carrier concentration. In this equation, when the MR is small, namely, $\rho(T,H)/\rho(T,0) \sim 1$, the equation can be simplified to a linear format, corresponding to the negative linear component, with:

$$\frac{\Delta\rho}{\rho} = \beta_1 B \quad (4)$$

where B is the applied magnetic field and β_1 is the coefficient for the linear component. The quadratic term is attributed to the shrinkage of localized electronic wave function in the magnetic field. For a localized carrier, the magnetic field will be equivalent to an additional potential. This magnetic barrier will squeeze the electronic wave function, reduce the overlap between neighbors, cause a lower hopping rate, which result in a positive MR²⁵:

$$\ln\left(\frac{\rho(H)}{\rho(0)}\right) = \frac{\tau a^* e^2 H^2}{N_i c^2 \hbar^2} \quad (5)$$

where τ is the scattering time, a^* is the localization radius of the electronic wave function and N_i is the doping level. When MR is small, the equation can be simplified to a quadratic format:

$$\frac{\Delta\rho}{\rho} = \beta_2 B^2 \quad (6)$$

where β_2 is the coefficient for the quadratic component.

In the metallic phase [Fig 4. (a)], as temperature drops, a transition from linear MR to quadratic MR is observed. Interestingly, we found it is also well fitted with a superposition of a linear part and quadratic part. However, MR behaviour in the high temperature is fewer focused than the low temperature, we need analyse the corresponding mechanism accordingly.

Two different models were proposed recently for the linear MR behaviour. The Quantum linear MR²⁶ is the one-landau-band limit of the SdH, with:

$$\frac{\Delta\rho}{\rho} = \frac{N_i H}{\pi n^2 e c}, \left[n < \left(\frac{eH}{ch}\right)^{\frac{3}{2}} \right] \quad (7)$$

For $n_e \sim 7 \times 10^{18} \text{cm}^{-3}$, it requires $B > 20\text{T}$, which is far beyond our measurement range. Besides, the linear MR here appears around room temperature, where quantum effects are usually eliminated by various scattering disturbance. Thus, this model is inconsistent with our experiment. The other model, classical linear MR²⁷, results from disorder scattering, with:

$$\frac{\Delta\rho}{\rho} \sim \frac{\pi \mu H}{2[g+0.35]} = \beta_1 B \quad (8)$$

where g is a numeric factor among 0 to 1. For the condition at 210K, where $B=9\text{T}$, $\mu \approx 50 \text{cm}^2/(\text{V}\times\text{s})$ and $\text{MR} \sim 0.18\%$, the calculated g is acceptable, around 0.26. Moreover, a sign for the classical linear MR is its independence on carrier concentration, which is clearly shown in Fig 4. (b).

For a quadratic MR, the common explanation is the Lorentz motion²⁸ with:

$$\frac{\Delta\rho}{\rho} \sim (\mu B)^2 \quad (9)$$

For $\mu \approx 50 \text{ cm}^2/(\text{V} \times \text{s})$, $B=9\text{T}$, the MR is around 0.01%, which is much smaller than the experimental value $\sim 0.2\%$. Such huge discrepancy indicates the Lorentz model is not applicable here. Noted that large polarons could protect the carrier from scattered by disorder²⁹, cooling will be beneficial for polaron formation, and the linearity of MR indeed decrease with dropping temperature, we assume that the MR transition from linear to quadratic is due to the formation of large polaron. When the polaron forms, the electron begins to self-trap. The magnetic field will add an additional magnetic potential to the system and perturb the electronic state¹⁹, resulting in a positive quadratic MR, as:

$$m_{\text{LP}} = \frac{E_{\text{LP}}}{\omega_{\text{LO}}^2 a^{*2}}, V_{\text{H}} = \frac{\hbar^2 a^{*2}}{8m\lambda^4} \quad (10)$$

$$\rho(H) = \frac{m^*}{ne^2\tau} = \frac{E_{\text{LP}}(H)}{ne^2\tau \cdot \omega_{\text{LO}}^2 a^{*2}} = \frac{E_{\text{LP}}(0) + V_{\text{H}}}{ne^2\tau \cdot \omega_{\text{LO}}^2 a^{*2}} \quad (11)$$

thus:

$$\frac{\Delta\rho}{\rho} = \frac{V_{\text{H}}}{E_{\text{LP}}} = \left(\frac{e}{m}\right)^2 \frac{B^2}{8\omega_{\text{LO}}^2} = \beta_2 B^2 \quad (12)$$

where $\lambda = \sqrt{\hbar/(eB)}$ is called magnetic length. With $B=9$, the MR is around 0.26%, consisting with our experimental result.

Discussion

During above discussion, we find: (1) a positive linear MR corresponds to the coherent motion of the carrier in a disorder system; while a negative MR indicates the incoherent hopping transport. (2) a small quadratic MR at high temperature results from the weak polaronic self-trapping; while a larger quadratic MR at low temperature represent a stronger defect trapping. Hence, the linear and quadratic terms can be interpreted as an indicator for the transport and trap condition of the carrier. Since different polaron state corresponds to different transport and trap state, MR can be used to infer the polaron evolution.

At high temperature, the thermal vibration would break the e-ph coupling, resulting in a dissociation state¹²⁻¹³. The electrons would be scattered by disorder and MR would be linear and independent of carrier concentration. In this state, when temperature decreases, the e-ph scattering are weakened, the mobility will increase as shown in Fig 2 (B), leading to an increasing β_1 . Besides, with attenuated thermal vibration, the polaronic effect would be strengthened, resulting in an increasing β_2 . These dissociation behaviours can be observed at the range from 210K to 300K in Fig.5.(a).

As the temperature keeps dropping, the system would finally transition to a typical large polaron system²³. Quadratic MR would dominate in this phase. And the linear coefficient β_1 would decrease since the formation of large polaron can protect the electron from scattered by disorder²⁹. Typically, at the low carrier concentration limit, the force among polaron is repulsive¹⁶. The polaron tends to be localized and hampers the increase of the mobility. However, if carrier concentration is so high that polarons start to overlap, the system

would become polaron liquid¹⁴⁻¹⁵. In the liquid phase, the e-ph interaction is attenuated, the carriers are more free and prone to various scattering mechanism. Hence, contrary to typical large polaron system, the liquid phase mobility would increase with dropping temperature. In Fig 5 (a), the 90K to 210K data consistent with above description.

When the temperature is low enough, the carriers start to drop from the CB to the trapping sites⁸, forming a localized polaron state⁷. The carrier transport type would transient from coherent transport to the incoherent hopping transport. The β_1 would change from positive to negative. Since the type of trapping change from the weak extensive spread self-trapping to a stronger localized defect trapping, a transient in β_2 should also be observed. Corresponding behaviour can be found at the temperature below 90K [Fig.5 (b)]. Besides, in β_2 around 60K, the transition between self-trapping and defect trapping is blurred above $\sim 4 \times 10^{19} \text{cm}^{-3}$, where the lattice starts to be relaxed [Fig1.(b)], polarons start to overlap and screening effect emerges¹⁰. Thus, we would choose this carrier concentration as the boundary for the liquid phase in the polaron evolution diagram. [Fig 5.(c)]

Conclusion

In summary, anatase TiO_2 samples was fabricated, covering mostly reported resistivity range from 10^{-1} to $10^{-4} \Omega \times \text{cm}$. A phase diagram for the polaron evolution was plotted through detailed analysis on the electro and magneto transport data. Our results filled the gap of study on large polaron evolution in anatase TiO_2 and built a bridge to understanding various reported anatase TiO_2 related transport experiments. We proved that anatase can be smoothly tuned from a weakly correlated metal to polaronic semiconductor through controlling the polaron state. This can help to engineer the TiO_2 based devices in industrial application.

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Figure Caption

Figure 1. (a) X-ray diffraction of as-grown and reduced TiO₂ films on LAO substrate. (b) Normalized intensity of X-ray scattering around the (004) Bragg reflection. The FWHM ratio of the reduced to the oxygen-rich sample is drawn in the inset of (b).

Figure 2.(a) Temperature dependence of resistivity in anatase TiO₂ thin film. (b) Carrier concentration and mobility measured by Hall effect. In 3-300K range, a higher carrier concentration always corresponds to a higher mobility. (c) Measured (symbols) and modelled (solid line) resistivity in the $7 \times 10^{18}\text{cm}^{-3}$ sample. Variable range hopping and polaron scattering are included. (d) Calculated effective mass of the large polaron.

Figure 3. (a) Magnetoresistance (MR) in the $7 \times 10^{18}\text{cm}^{-3}$ sample. (b)-(d) MR of samples with different carrier concentration at 60K, 10K and 3K (e) Experimental and fitting curves of MR for the $7 \times 10^{18}\text{cm}^{-3}$ sample at 60K, 10K and 3K. The MR can be well decomposed to a negative linear component and a quadratic component. This applies to all the samples.

Figure 4. (a) Fine structure of MR in the $7 \times 10^{18}\text{cm}^{-3}$ sample in high temperature (>120K). (b)-(d) MR of samples with different carrier concentration at 300K, 210K and 120K (e) Experimental and fitting curves of MR for the $7 \times 10^{18}\text{cm}^{-3}$ sample at 300K, 210K and 120K. MR in high temperature can also be well decomposed to a linear component and a quadratic component.

Figure 5. (a)-(b) The temperature dependent of parameter β_1 and β_2 of the Anatase samples. (c) Phase diagram for large polaron in anatase TiO₂, where we have sketched the proposed polaron phases and how it might evolve according to temperature and carrier concentration. The boundary 1 circle points are the maximum values of β_1 , separating the dissociation phase from the polaronic phases. The boundary 2 square points are zero points of β_1 , separating the localized state from the mobile states.

Fig.1

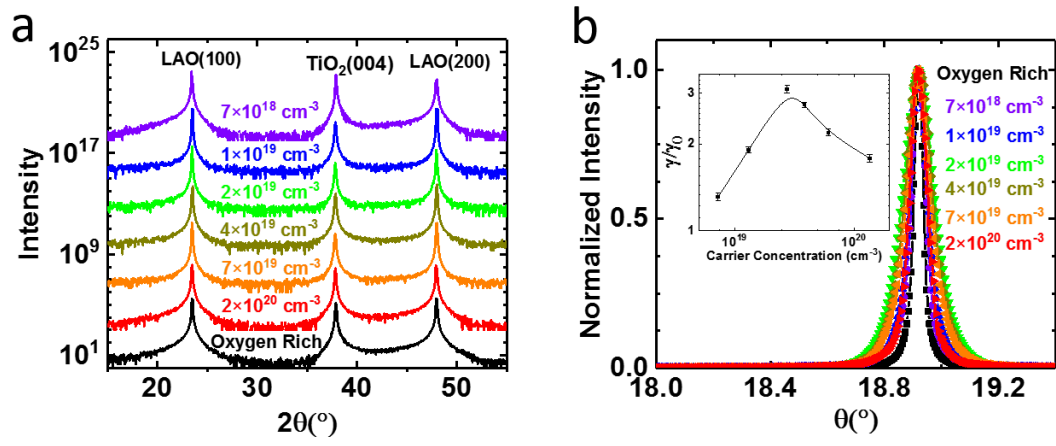


Fig.2

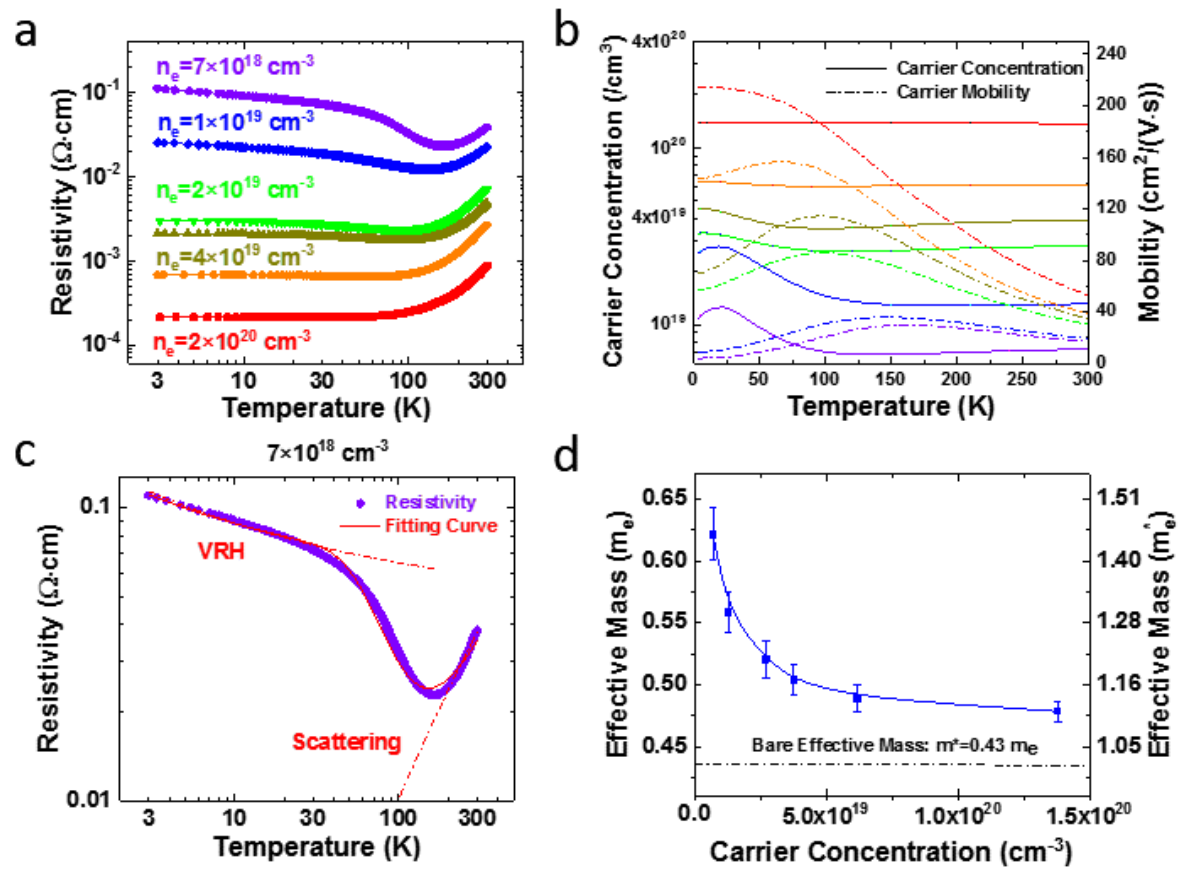


Fig.3

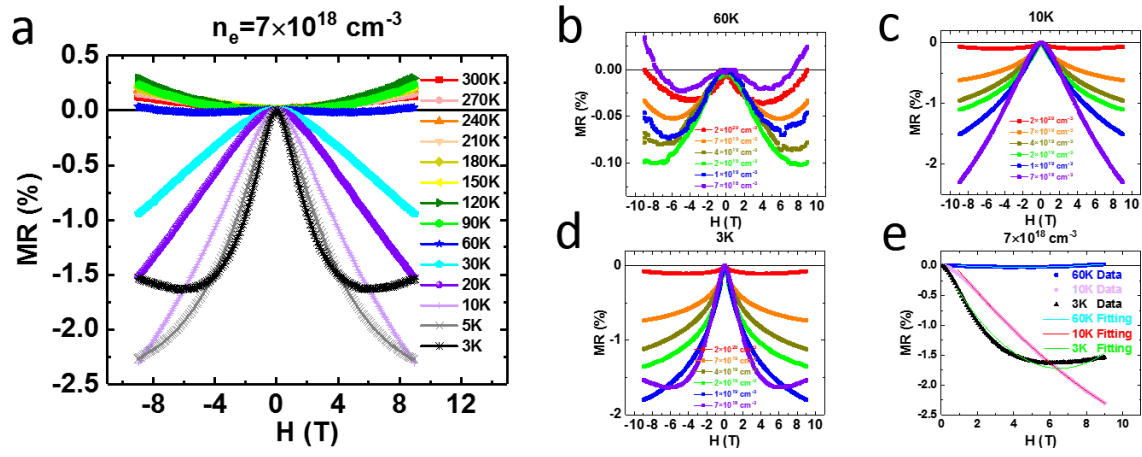


Fig.4

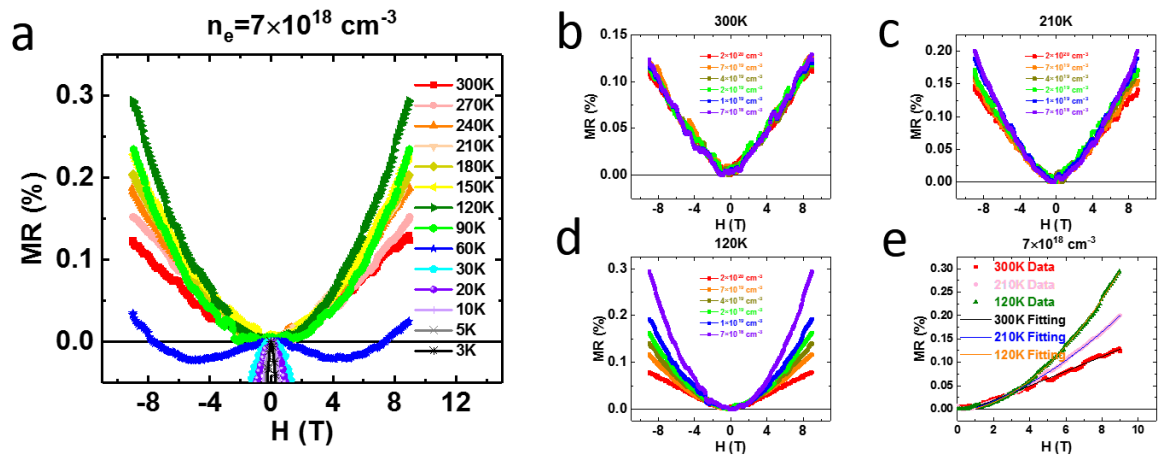


Fig.5

